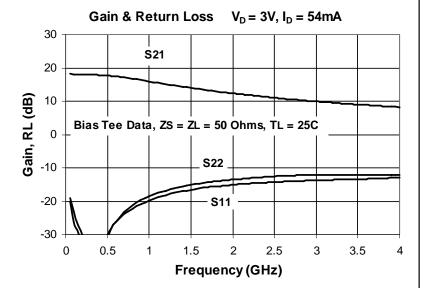
SIRENZA MICRODEVICES Product Description

Sirenza Microdevices' SGC-4386Z is a high performance SiGe HBT MMIC amplifier utilizing a Darlington configuration with a patented active bias network. The active bias network provides stable current over temperature and process Beta variations. Designed to run directly from a 3V supply, the SGC-4386Z does not require a dropping resistor as compared to typical Darlington amplifiers. The SGC-4386Z is designed for high linearity 3V gain block applications that require small size and minimal external components. It is internally matched to 50 ohms.



SGC-4386Z

50-4000 MHz Active Bias Silicon Germanium Cascadable Gain Block





Product Features

- Single Fixed 3V Supply
- No Dropping Resistor Required
- Patented Self-Bias Circuitry
- P1dB = 12.7 dBm at 1950 MHz
- OIP3 = 27 dBm at 1950 MHz
- Robust 1000V ESD, Class 1C HBM

Applications

- PA Driver Amplifier
- Cellular, PCS, GSM, UMTS, WCDMA
- IF Amplifier
- Wireless Data, Satellite

Symbol	Parameters	Units	Frequency	Min.	Тур.	Max.
			850 MHz	15.2	16.7	18.2
G	Small Signal Gain	dB	1950 MHz	11.2	12.7	14.2
			2400 MHz		10.9	
			850 MHz		13.4	
P _{1dB}	Output Power at 1dB Compression	dBm	1950 MHz	11.7	12.7	
			2400 MHz		11.8	
	Output Third Order Intercept Point	dBm	850 MHz		29.5	
OIP ₃			1950 MHz	25.0	27.0	
			2400 MHz		26.0	
IRL	Input Return Loss	dB	1950 MHz	11	15.0	
ORL	Output Return Loss	dB	1950 MHz	9.5	13.5	
NF	Noise Figure	dB	1930 MHz		3.7	4.7
V _D	Device Operating Voltage	V			3	
Ι _D	Device Operating Current	mA		48	54	60
Rth, j-l	Thermal Resistance (junction to lead)	°C/W			145	
Test Conditions: $V_D = 3.0V$ $I_D = 54mA Typ.$ $T_L = 25$		5°C	OIP ₃ Tone	e Spacing =	1MHz	
Bias Tee Data $Z_S = Z_L = 50$ Ohms Pout per tone = -5 dBm						

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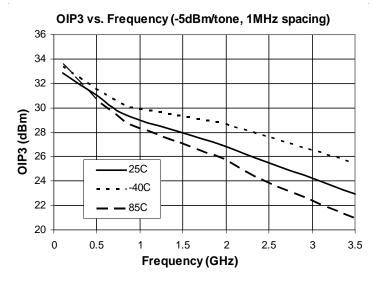
303 S. Technology Ct. Broomfield, CO 80021

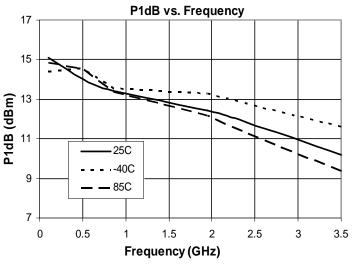
http://www.sirenza.com EDS-104976 Rev C



Symbol	Parameter	Unit	Frequency (MHz)					
		onin	100	500	850	1950	2400	3500
G	Small Signal Gain	dB	18.1	17.6	16.7	12.7	10.9	8.6
OIP ₃	Output Third Order Intercept Point	dBm	32.5	31.0	29.5	27.0	26.0	23.0
P _{1dB}	Output Power at 1dB Compression	dBm	15.1	14.0	13.4	12.7	11.8	10.2
IRL	Input Return Loss	dB	29.0	24.0	24.5	15.0	14.5	13.0
ORL	Output Return Loss	dB	27.0	24.0	22.5	13.5	13.0	12.0
S ₁₂	Reverse Isolation	dB	20.0	21.5	21.5	19.5	19.0	18.0
NF	Noise Figure	dB	2.9	3.0	3.4	3.7	4.1	5.0

Typical Performance with Bias Tee, $V_{D} = 3V$, $I_{D} = 54mA$





and testing devices must be observed.

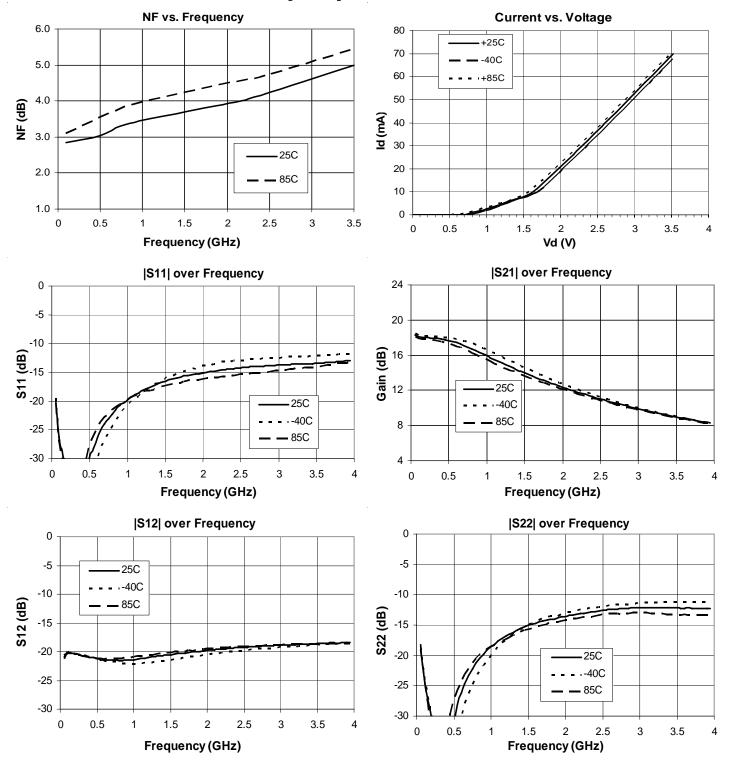
Absolute Maximu	m Ratings	Reliability & Qualification Information			
Parameter	Absolute Limit	Parameter	Rating		
Max Device Current (I _{CE})	110 mA	ESD Rating - Human Body Model (HBM)	Class 1C		
Max Device Voltage (V _{CE})	4.5 V				
Max. RF Input Power* (See Note)	+18 dBm	Moisture Sensitivity Level	MSL 1		
Max. Junction Temp. (T _J)	+150°C	This product qualification report can be downloaded at			
Operating Temp. Range (T _L)	-40°C to +85°C	www.sirenza.com			
Max. Storage Temp.	+150°C	Caution: ESD sensitive			
*Note: Load condition, Z _L = 50 Ohms		Appropriate precautions in handling, packaging			

Operation of this device beyond any one of these limits may cause permanent damage. For reliable continuous operation, the device voltage and current must not exceed the maximum operating values specified in the table on page one.

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Typical Performance with Bias Tee, $V_D = 3V$, $I_D = 54mA$



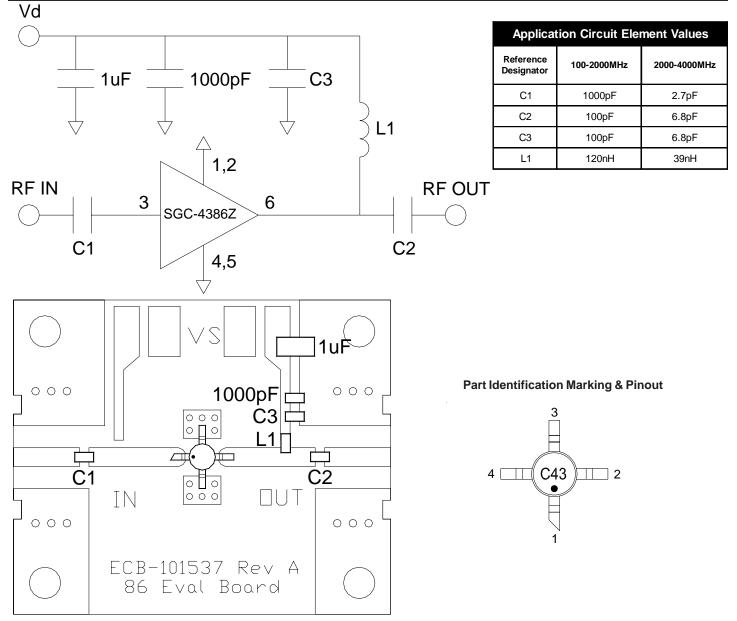
303 S. Technology Ct. Broomfield, CO 80021 Phone: (800) SMI-MMIC

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www.DataSheet4U.com



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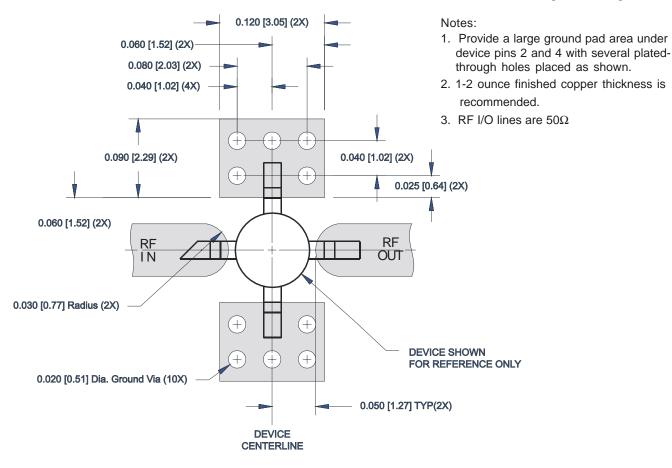
Pin #	Function	Description	Part / Evaluation Board Ordering Information				
1		RF input pin. This pin requires the use of an external DC blocking capacitor chosen for the frequency of operation	Part Number	Description	Reel Size	Devices / Reel	
2,4	GND	Connection to ground. Use via holes as close to the device ground leads as possible to reduce ground inductance and achieve optimum RF performance	SGC-4386Z	Lead Free, RoHs Compliant	13"	3000	
			SGC-4386Z-EVB1	100-2000 MHz Evaluation Board	N/A	N/A	
	RF OUT /	RF output and bias pin. This pin requires the use of an	SGC-4386Z-EVB2	2000-4000 MHz Evaluation Board	N/A	N/A	
3	DC BIAS	avternal D(blocking canacitor chosen for the trequency of					

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86 PCB Pad Layout

Dimensions in inches [millimeters]



86 Nominal Package Dimensions

Dimensions in inches [millimeters] A link to the 86 package outline drawing with full dimensions and tolerances may be found on the product web page at www.sirenza.com.

